

ABSTRACT

An ohmic electrode structure of a nitride semiconductor device having a
5 nitride semiconductor. The ohmic electrode structure is provided with a first
metal film formed on the nitride semiconductor and a second metal film formed
on the first metal film. The first metal film is composed of at least one material
selected from a group consisting of V, Mo, Ti, Nb, W, Fe, Hf, Re, Ta and Zr.
The second metal film is composed of at least one material different from that of
10 the first metal film (102), selected from a group consisting of V, Mo, Ti, Nb, W,
Fe, Hf, Re, Ta, Zr, Pt and Au.